



(b) The principal embodiment.

1: n-type InP substrate, 2: n-type InP layer, 3: GaInAsP active layer, 3A: active region, 4: p-type InP layer, 5: SiO₂ layer, 6: mirror facet, 7: Au-Zn metallic electrode, 7A: opening in the electrode, 8: Au-Sn metallic electrode, 8A: opening in the electrode, 9: Au layer, 10: surface-emitting semiconductor laser, 11: light propagation loop, and 12: laser light output.

Fig. 10 VCSEL Patent, Titech